

**ABSTRACT OF THE DISCLOSURE**

A3

A pattern correcting method of a mask for manufacturing a semiconductor device includes extracting a correction portion to be corrected from a mask pattern on the mask, obtaining a surrounding environment of the correction portion and giving a correction amount to the correction portion. The correction amount is variable. The variable correction amount is given to the correction portion in accordance with the surrounding environment of the correction portion.

FINNEGAN  
HENDERSON  
FARABOW  
GARRETT &  
DUNNER LLP

1300 I Street, NW  
Washington, DC 20005  
202.408.4000  
Fax 202.408.4400  
[www.finnegan.com](http://www.finnegan.com)